MSKSEMI 美森科













FSD

TVS

TSS

MOV

GDT

PLED

AO4430

Product specification





General Features

- 30 V, 16A, RDS(ON)=4.8mΩ@VGS = 10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

Application

- Notebook
- Load Switch
- LED applications
- Hand-Held Device

Reference News

PACKAGE OUTLINE	Pin Configuration	Marking
SOP-8	G S	MSKSEMI 4430 MS30N



Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
	Drain-Source Voltage	·	
V _{DS}	·	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (T _C =250)	16	А
	Drain Current – Continuous (T _C =1000)	9.5	А
I _{DM}	Drain Current – Pulsed ¹	60	А
P _D	Power Dissipation (T _C =250)	4	W
	Power Dissipation – Derate above 250	0.032	W/ C
T _{STG}	Storage Temperature Range	-55 to 150	С
TJ	Operating Junction Temperature Range	-55 to 150	С

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
R _{0JA}	Thermal Resistance Junction to ambient	·	85	C/ W
R ₀ JC	Thermal Resistance Junction to Case		31	C/ W

Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V
△BV _{DSS} /△T _J	BV _{DSS} Temperature Coefficient	Reference to 250 , I _D =1mA		0.04		V/ C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V , V _{GS} =0V , T _J =250			1	uA
IDSS		V _{DS} =24V , V _{GS} =0V , T _J =1250			10	uA
Igss	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA



On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V , I _D =6A		4.8	8	mΩ
TOS(ON)		V _{GS} =4.5V , I _D =3A		7.5	14	Ω_{m}
V _{GS(th)}	Gate Threshold Voltage		1.2	1.5	2.5	V
	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =250uA				
$\triangle V_{GS(th)}$				-4		mV/ C
gfs	Forward Transconductance	V _{DS} =10V , I _D =10A		18		S

Dynamic and switching Characteristics

Dynamic	and Switching	Characteristics			
Q_g	Total Gate Charge ^{2, 3}			7.5	
Q_{gs}	Gate-Source Charge ^{2, 3}	V _{DS} =15V , V _{GS} =4.5V , I _D =10A		1.3	 nC
Q _{gd}	Gate-Drain Charge ^{2, 3}			4.5	
T _{d(on)}	Turn-On Delay Time ^{2, 3}			4.8	
Tr	Rise Time ^{2,3}	V_{DD} =15V , V_{GS} =10V , R_{G} =3.3 Ω		12.5	 ns
T _{d(off)}	Turn-Off Delay Time ^{2, 3}	In=15A		27.6	
T _f	Fall Time ^{2,3}			8.2	
Ciss	Input Capacitance			750	
Coss	Output Capacitance	V _{DS} =25V , V _{GS} =0V , F=1MHz		150	 pF
Crss	Reverse Transfer Capacit	ance		110	
Rg	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		2.7	 Ω

Drain- Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	V _G =V _D =0V , Force Current			16	Α
I _{SM}	Pulsed Source Current	VG-VD-0V , I GICE Current			32	Α
V _{SD}	Diode Forward Voltage	V _{GS} =0V , I _S =1A , T _J =250			1.2	V

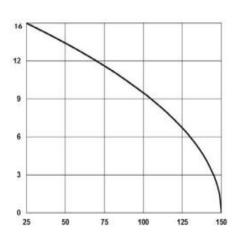
Note:

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2. The data tested by pulsed , pulse width $\leq 300\,\mathrm{us}$, duty cycle $\leq 2\%$.
- 3. Essentially independent of operating temperature.

In , Continuous Drain Current (A)

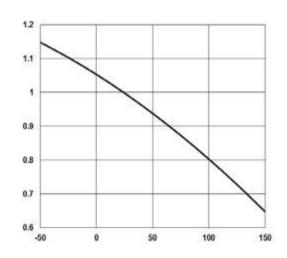
Normalized Gate Threshold Voltage (V)

Normalized Thermal Response (Reuc)



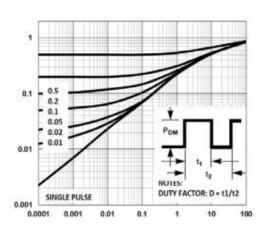
 T_C , Case Temperature (°C)

Fig. 1 Continuous Drain Current vs. T_c



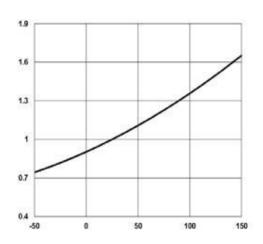
 T_J , Junction Temperature (°C)

Fig. 3 Normalized V_{th} vs. T_J



Square Wave Pulse Duration (s) Fig. 5 Normalized Transient Impedance

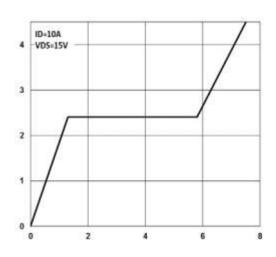
Normalized On Resistance (m^{Ω})



T_J, Junction Temperature (°C)

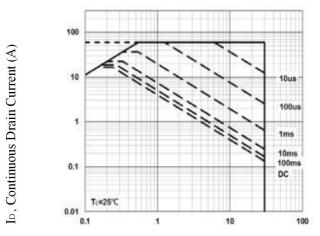
Fig. 2 Normalized RDSON vs. T_J

 V_{GS} , Gate to Source Voltage (V)



Qg, Gate Charge (nC)

Fig. 4 Gate Charge Waveform



V_{DS}, Drain to Source Voltage (V)

Fig. 6 Maximum Safe Operation Area

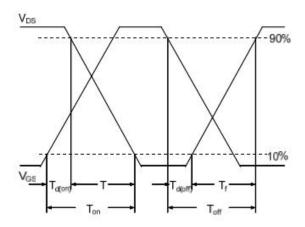
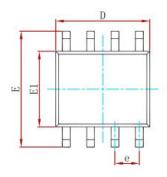
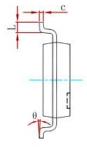


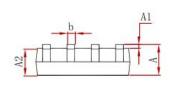
Fig. 7 Switching Time Waveform



PACKAGE MECHANICAL DATA

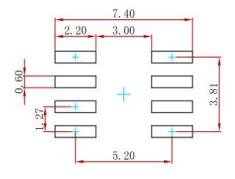






Symbol	Dimensions In	Millimeters	Dimensions	In Inches
Symbol	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0. 100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0. 170	0.250	0.007	0.010
D	4.800	5.000	0.189	0. 197
e	1. 270 (BSC)		0.050	(BSC)
Е	5. 800	6.200	0. 228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0.0	8°	0.0	8°

Suggested Pad Layout



- Note:
 1.Controlling dimension:in millimeters.
 2.General tolerance:±0.05mm.
 3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AO4430	SOP8	3000



Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer'sproducts or equipment.
- MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents—or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by MSKSEMI manufacturer:

Other Similar products are found below:

IRFD120 JANTX2N5237 2SK2267(Q) BUK455-60A/B TK100A10N1,S4X(S MIC4420CM-TR VN1206L NDP4060 SI4482DY IRS2092STRPBF-EL IPS70R2K0CEAKMA1 TK31J60W5,S1VQ(O TK31J60W,S1VQ(O TK16J60W,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1 DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1 MCQ7328-TP SSM3J143TU,LXHF DMN12M3UCA6-7 PJMF280N65E1_T0_00201 PJMF380N65E1_T0_00201 PJMF900N60E1_T0_00201